

PRELIMINARY

Notice: This is not a final specification.  
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR &lt;TRANSISTOR ARRAY&gt;

**M63805P/FP/KP**

8-UNIT 300mA TRANSISTOR ARRAY

**DESCRIPTION**

M63805P/FP/KP are eight-circuit Single transistor arrays. The circuits are made of NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

**FEATURES**

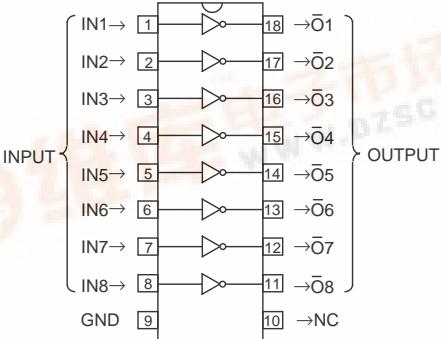
- Three package configurations (P, FP, and KP)
- Medium breakdown voltage ( $BV_{CEO} \geq 35V$ )
- Synchronizing current ( $I_c(max) = 300mA$ )
- With zener diodes
- Low output saturation voltage
- Wide operating temperature range ( $T_a = -40$  to  $+85^{\circ}C$ )

**APPLICATION**

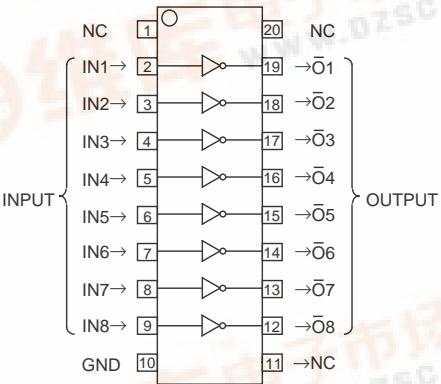
Driving of digit drives of indication elements (LEDs and lamps) with small signals

**FUNCTION**

The M63805P/FP/KP each have eight circuits consisting of NPN transistor. The transistor emitters are all connected to the GND pin. The transistors allow synchronous flow of 300mA collector current. A maximum of 35V voltage can be applied between the collector and emitter.

**PIN CONFIGURATION**

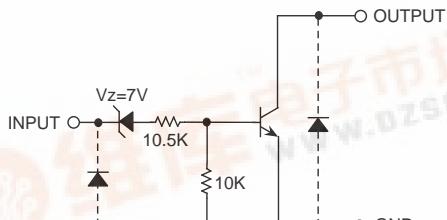
Package type 18P4G(P)



NC : No connection

20P2N-A(FP)

Package type 20P2E-A(KP)

**CIRCUIT DIAGRAM**

The eight circuits share the GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit:  $\Omega$

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**ABSOLUTE MAXIMUM RATINGS** (Unless otherwise noted,  $T_a = -40 \sim +85^\circ\text{C}$ )

Symbol	Parameter	Conditions	Ratings	Unit
VCEO	Collector-emitter voltage	Output, H	-0.5 ~ +35	V
IC	Collector current	Current per circuit output, L	300	mA
VI	Input voltage		-0.5 ~ +35	V
Pd	Power dissipation	$T_a = 25^\circ\text{C}$ , when mounted on board	M63805P	1.79
			M63805FP	1.10
			M63805KP	0.68
Topr	Operating temperature		-40 ~ +85	°C
Tstg	Storage temperature		-55 ~ +125	°C

**RECOMMENDED OPERATING CONDITIONS** (Unless otherwise noted,  $T_a = -40 \sim +85^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
Vo	Output voltage		0	—	35	V
IC	Collector current (Current per 1 circuit when 8 circuits are coming on simultaneously)	M63805P	Duty Cycle no more than 50%	0	—	250
			Duty Cycle no more than 100%	0	—	170
		M63805FP	Duty Cycle no more than 30%	0	—	250
			Duty Cycle no more than 100%	0	—	130
		M63805KP	Duty Cycle no more than 12%	0	—	250
			Duty Cycle no more than 100%	0	—	100
VIN	Input voltage		0	—	30	V

**ELECTRICAL CHARACTERISTICS** (Unless otherwise noted,  $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
V (BR) CEO	Collector-emitter breakdown voltage	$I_{CEO} = 10\mu\text{A}$	35	—	—	V
VCE(sat)	Collector-emitter saturation voltage	$I_{IN} = 1\text{mA}$ , $I_C = 10\text{mA}$	—	—	0.2	V
		$I_{IN} = 2\text{mA}$ , $I_C = 150\text{mA}$	—	—	0.8	
VIN(on)	"On" input voltage	$I_{IN} = 1\text{mA}$ , $I_C = 10\text{mA}$	13	19	23	V
hFE	DC amplification factor	$V_{CE} = 10\text{V}$ , $I_C = 10\text{mA}$	50	—	—	—

**SWITCHING CHARACTERISTICS** (Unless otherwise noted,  $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
ton	Turn-on time	$CL = 15\text{pF}$ (note 1)	—	140	—	ns
toff	Turn-off time		—	240	—	ns

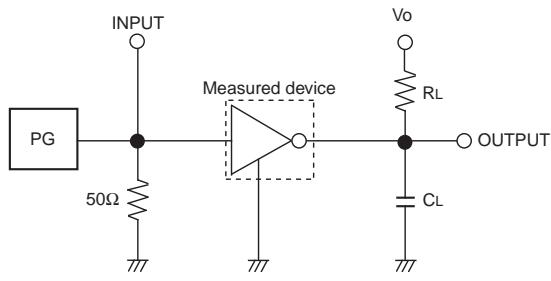
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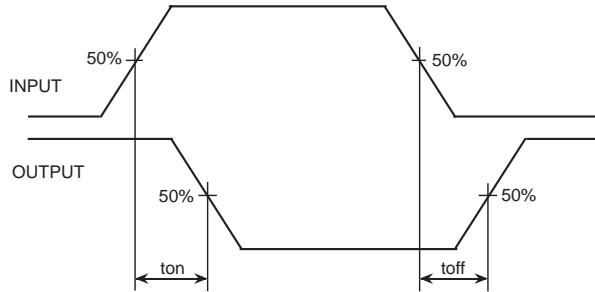
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#### NOTE 1 TEST CIRCUIT

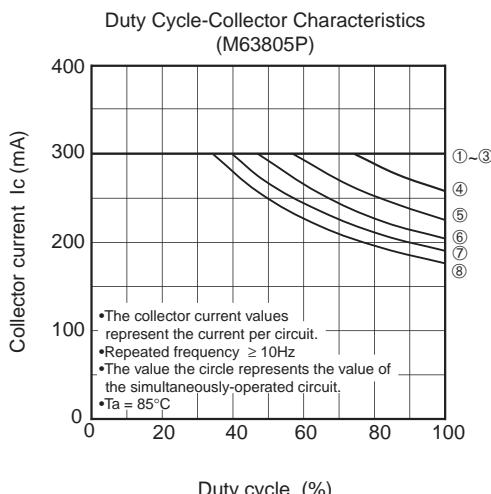
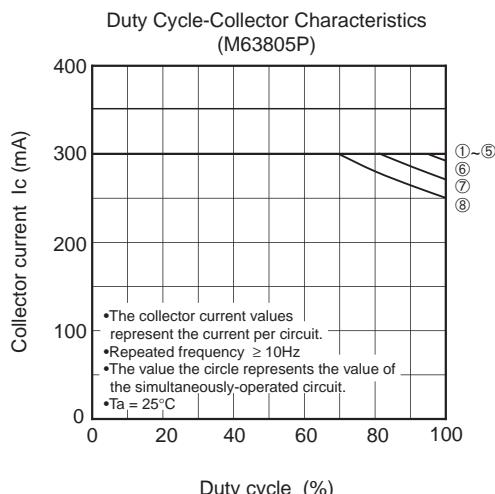
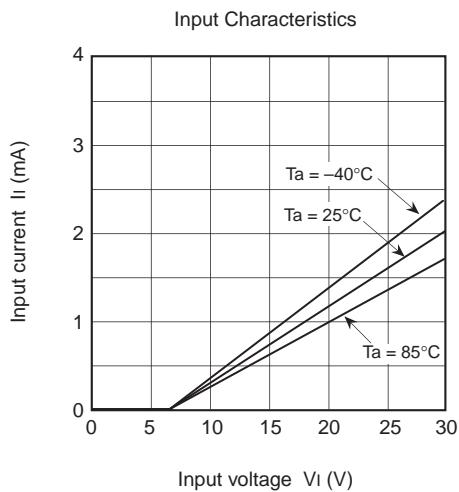
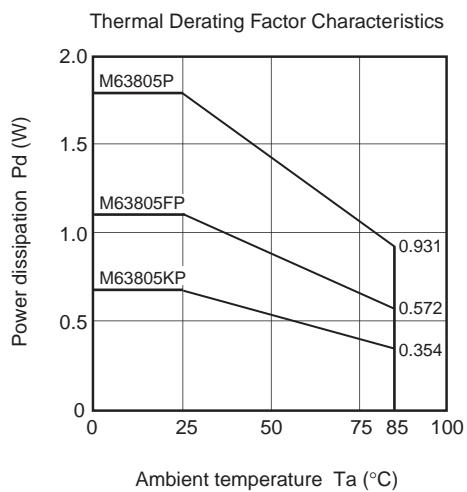


- (1) Pulse generator (PG) characteristics : PRR = 1kHz,  $t_w = 10\mu s$ ,  $t_r = 6ns$ ,  $t_f = 6ns$ ,  $Z_0 = 50\Omega$ ,  $V_{IH} = 18V$
- (2) Input-output conditions :  $R_L = 220\Omega$ ,  $V_o = 35V$
- (3) Electrostatic capacity  $C_L$  includes floating capacitance at connections and input capacitance at probes

#### TIMING DIAGRAM



#### TYPICAL CHARACTERISTICS



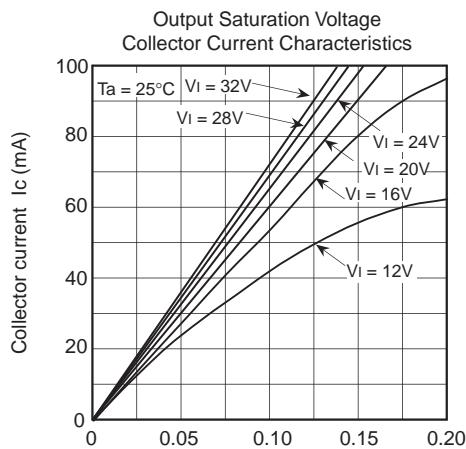
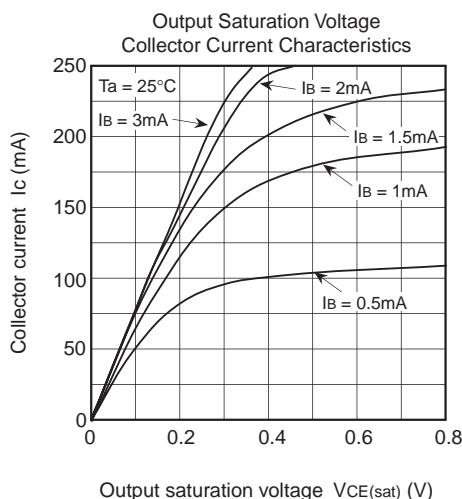
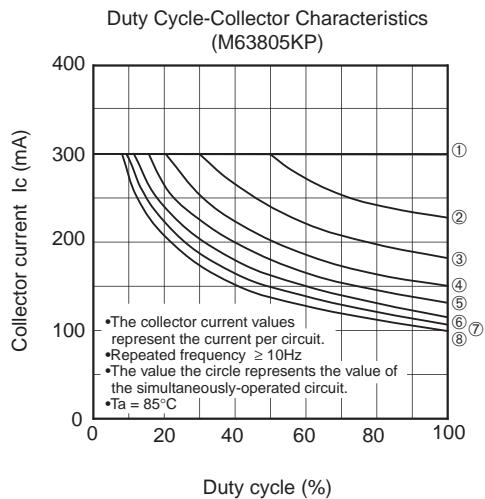
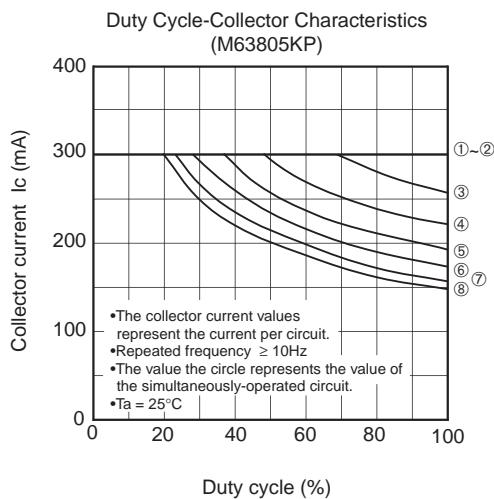
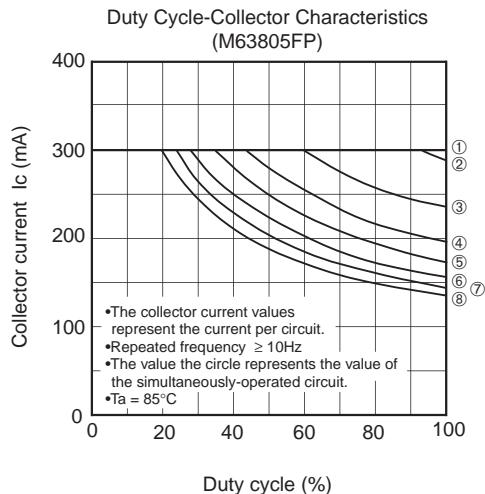
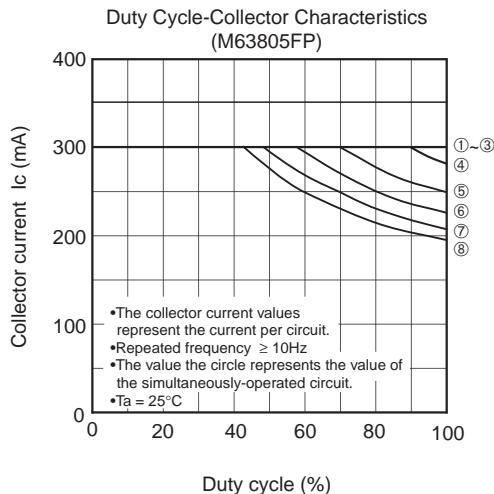
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